TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ( $\pi$ -MOSIV)

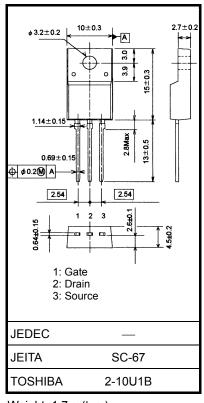
# 2SK4013

#### Switching Regulator Applications

- Low drain-source ON resistance:  $R_{DS (ON)} = 1.35 \Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 5.0 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS}$  = 100  $\mu$ A (max) (V<sub>DS</sub> = 640 V)
- Enhancement-model:  $V_{th}$  = 2.0 to 4.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

| Characteristics                                      |       |          | Symbol           | Rating     | Unit |  |
|--|-------|----------|------------------|------------|------|--|
| Drain-source voltage                                 |       |          | V <sub>DSS</sub> | 800        | V    |  |
| Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ ) |       |          | V <sub>DGR</sub> | 800        | V    |  |
| Gate-source voltage                                  |       |          | V <sub>GSS</sub> | ±30        | V    |  |
| Drain current  | DC    | (Note 1) | ID               | 6          | А    |  |
|  | Pulse | (Note 1) | I <sub>DP</sub>  | 18         | A    |  |
| Drain power dissipation (Tc = $25^{\circ}$ C)        |       |          | PD               | 45         | W    |  |
| Single pulse avalanche energy<br>(Note 2)            |       |          | E <sub>AR</sub>  | 317        | mJ   |  |
| Avalanche current                                    |       |          | I <sub>AR</sub>  | 6          | А    |  |
| Repetitive avalanche energy (Note 3)                 |       |          | E <sub>AR</sub>  | 4.5        | mJ   |  |
| Channel temperature                                  |       |          | T <sub>ch</sub>  | 150        | °C   |  |
| Storage temperature range                            |       |          | T <sub>stg</sub> | -55 to 150 | °C   |  |

#### Absolute Maximum Ratings (Ta = 25°C)



Weight: 1.7 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

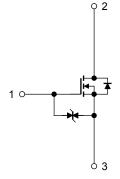
| Characteristics                        | Symbol                 | Max  | Unit |  |
|--|------------------------|------|------|--|
| Thermal resistance, channel to case    | R <sub>th (ch-c)</sub> | 2.78 | °C/W |  |
| Thermal resistance, channel to ambient | R <sub>th (ch-a)</sub> | 62.5 | °C/W |  |

Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:  $V_{DD} = 90 \text{ V}, \text{ T}_{ch} = 25^{\circ}\text{C}$  (initial), L = 14.5 mH, R<sub>G</sub> = 25  $\Omega$ , I<sub>AR</sub> = 6 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature.

This transistor is an electrostatic sensitive device. Please handle with caution.



Start of commercial production 2007-07

Unit: mm

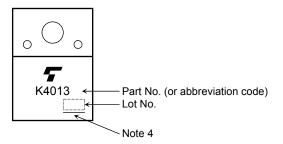
**Electrical Characteristics (Ta = 25°C)** 

| Characteristics                                    |                                | Symbol               | Test Condition   | Min | Тур. | Max | Unit |
|--|--------------------------------|----------------------|--|-----|------|-----|------|
| Gate leakage current                               |                                | I <sub>GSS</sub>     | $V_{GS}=\pm 25~V,~V_{DS}=0~V$  | _   |      | ±10 | μA   |
| Drain-source bre                                   | Drain-source breakdown voltage |                      | $I_G=\pm 10~\mu A,~V_{DS}=0~V$   | ±30 | _    | _   | V    |
| Drain cut-OFF cu                                   | rain cut-OFF current           |                      | $V_{DS} = 640 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$   | _   | _    | 100 | μA   |
| Drain-source breakdown voltage                     |                                | V (BR) DSS           | $I_D=10\ mA,\ V_{GS}=0\ V$   | 800 | _    | _   | V    |
| Gate threshold voltage                             |                                | V <sub>th</sub>      | $V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$  | 2.0 | _    | 4.0 | V    |
| Drain-source ON resistance                         |                                | R <sub>DS (ON)</sub> | $V_{GS} = 10 \text{ V}, \text{ I}_{D} = 3 \text{ A}$   | _   | 1.35 | 1.7 | Ω    |
| Forward transfer admittance                        |                                | Y <sub>fs</sub>      | $V_{DS} = 20 \text{ V}, \text{ I}_{D} = 3 \text{ A}$   | 2.5 | 5.0  | _   | S    |
| Input capacitance                                  |                                | C <sub>iss</sub>     |  | _   | 1400 | _   | pF   |
| Reverse transfer capacitance                       |                                | C <sub>rss</sub>     | $V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ f} = 1 \text{ MHz}$   | _   | 30   | _   |      |
| Output capacitance                                 |                                | C <sub>oss</sub>     |  | _   | 130  | _   |      |
| Switching time                                     | Rise time                      | tr                   | $V_{GS}^{10 V}$ $I_D = 3 A V_{OUT}$  |     | 25   |     |      |
|  | Turn-ON time                   | t <sub>on</sub>      |  |     | 80   |     | 20   |
|  | Fall time                      | t <sub>f</sub>       | $\begin{array}{c c} & & & \\ & & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & & & \\ & &$ |     | 65   |     | - ns |
|  | Turn-OFF time                  | t <sub>off</sub>     |  | —   | 220  | —   |      |
| Total gate charge<br>(gate-source plus gate-drain) |                                | Qg                   |  |     | 45   |     |      |
| Gate-source charge                                 |                                | Q <sub>gs</sub>      | $V_{DD} \simeq 400 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 6 \text{ A}$  | _   | 25   | _   | nC   |
| Gate-drain ("miller") charge                       |                                | Q <sub>gd</sub>      |  | _   | 20   | _   |      |

#### Source-Drain Ratings and Characteristics (Ta = 25°C)

| Characteristics                           | Symbol           | Test Condition                                | Min | Тур. | Max  | Unit |
|---|------------------|---|-----|------|------|------|
| Continuous drain reverse current (Note 1) | I <sub>DR</sub>  | —   | _   | _    | 6    | А    |
| Pulse drain reverse current (Note 1)      | I <sub>DRP</sub> | —   | _   | _    | 18   | А    |
| Forward voltage (diode)                   | V <sub>DSF</sub> | $I_{DR} = 6 \text{ A}, V_{GS} = 0 \text{ V}$  | _   | _    | -1.7 | V    |
| Reverse recovery time                     | t <sub>rr</sub>  | I <sub>DR</sub> = 6 A, V <sub>GS</sub> = 0 V, | _   | 1100 | _    | ns   |
| Reverse recovery charge                   | Q <sub>rr</sub>  | dI <sub>DR</sub> /dt = 100 A/μs               | _   | 10   |      | μC   |

### Marking

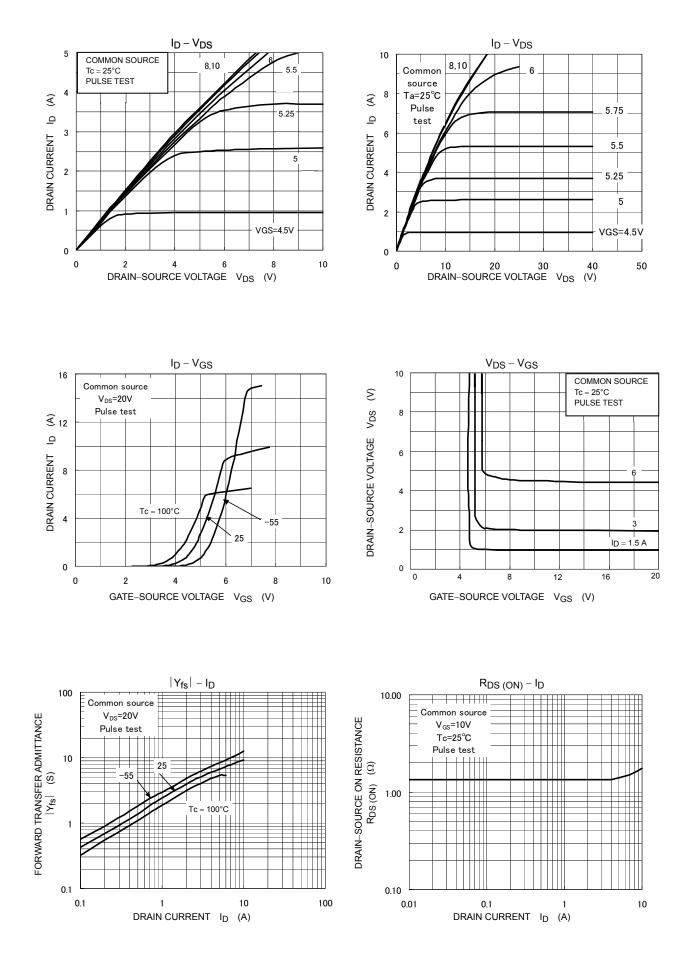


Note 4: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV

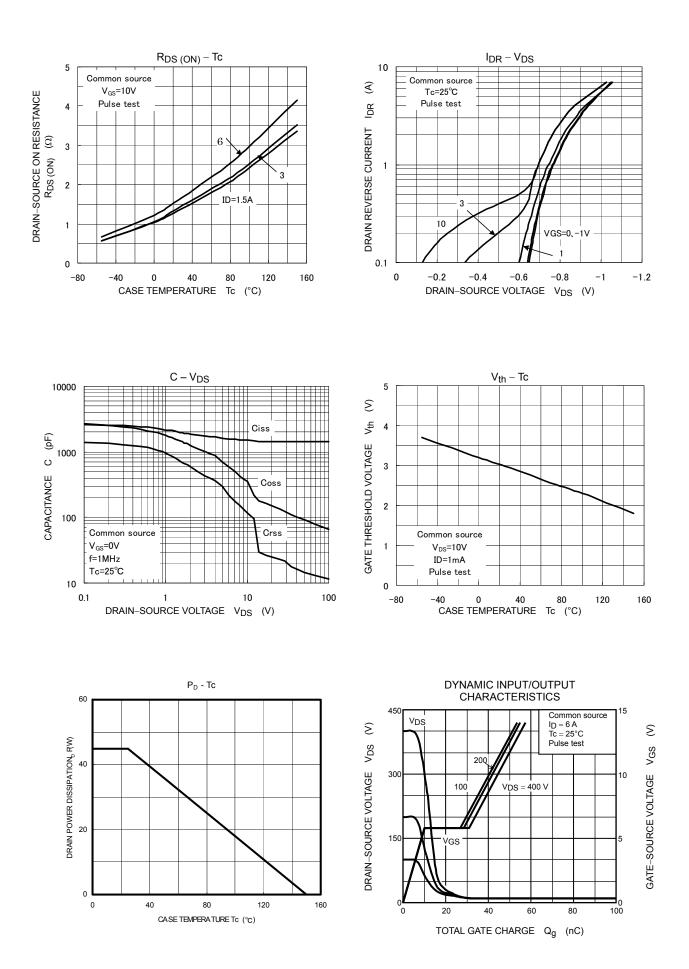
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

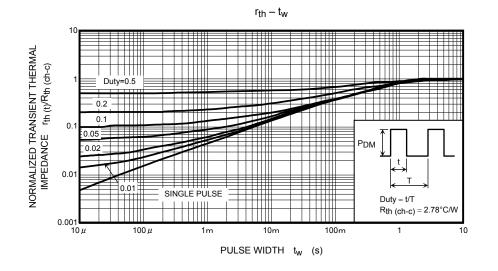
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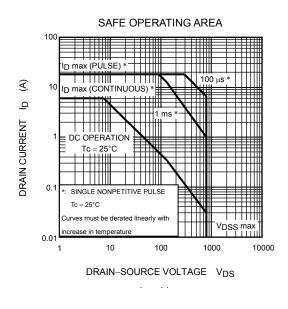
## **TOSHIBA**

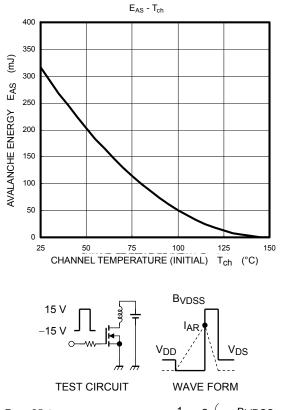


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$$R_{G} = 25 \Omega$$

$$V_{DD} = 90 V, L = 14.5 mH$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot l^{2} \cdot \left(\frac{BVDSS}{BVDSS - VDD}\right)$$

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